TSV521, TSV522, TSV524, TSV521A, TSV522A, TSV524A

High merit factor (1.15 MHz for 45 µA) CMOS op amps

Datasheet − preliminary data

Features

- Gain bandwidth product: 1.15 MHz typ. at 5 V
- Low power consumption: 45 µA typ. at 5 V
- Rail-to-rail input and output
- Low input bias current: 1 pA typ.
- Supply voltage: 2.7 to 5.5 V
- Low offset voltage: 800 µV max.
- Unity gain stable on 100 pF capacitor
- Automotive grade

Benefits

- Increased lifetime in battery powered applications
- Easy interfacing with high impedance sensors

Related products

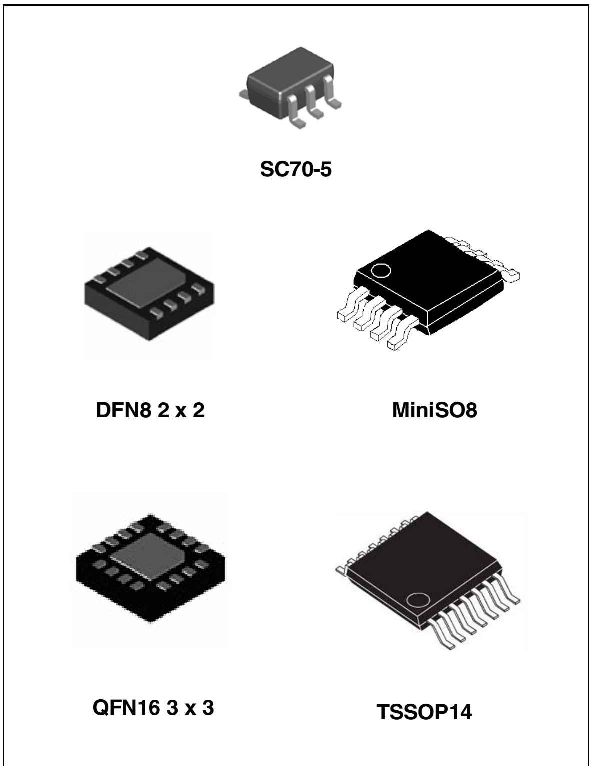
- See TSV6x series for lower minimum supply voltage (1.5 V)
- See LMV82x series for higher gain bandwidth products (5.5 MHz)

Applications

- Battery powered applications
- Portable devices
- Automotive signal conditioning
- Active filtering
- Medical instrumentation

Description

The TSV52x series of operational amplifiers offers low voltage operation and rail-to-rail input and output. The TSV521 device is the single version, the TSV522 device the dual version, and the TSV524 device the quad version, with pinouts compatible with industry standards.



The TSV52x series offers an outstanding speed/power consumption ratio, 1.15 MHz gain bandwidth product while consuming only 45 µA at 5 V. The devices are housed in the smallest industrial packages.

These features make the TSV52x family ideal for sensor interfaces, battery supplied and portable applications. The wide temperature range and high ESD tolerance facilitate their use in harsh automotive applications.

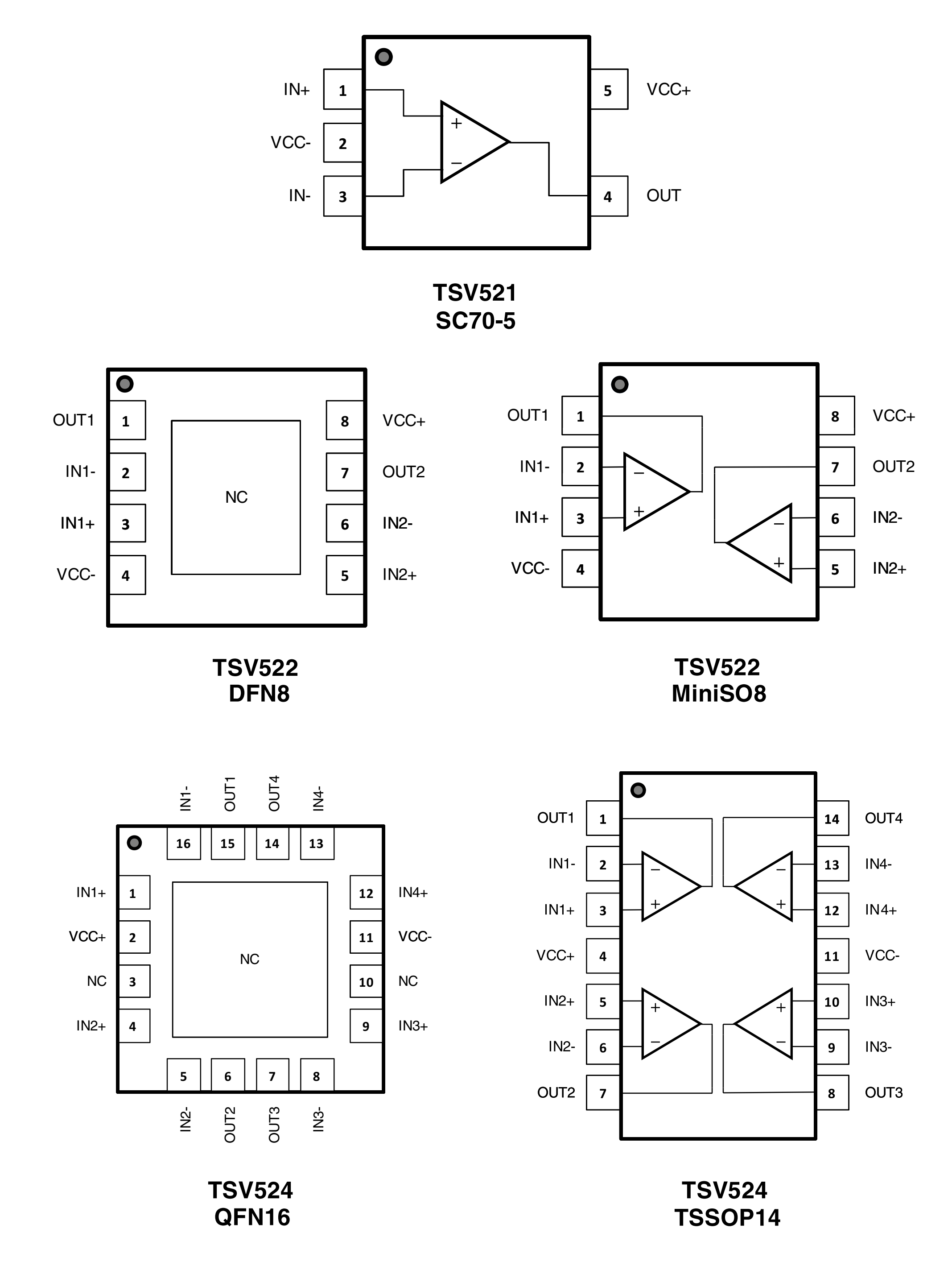
Table 1. Device summary

	Standard V_{io}	Enhanced V_{io}
Single	TSV521	TSV521A
Dual	TSV522	TSV522A
Quad	TSV524	TSV524A

Contents

1 Package pin connections

Figure 1. Pin connections for each package (top view)



2 Absolute maximum ratings and operating conditions

Table 2. Absolute maximum ratings (AMR)

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage[(1)]	6	V
V_{id}	Differential input voltage[(2)]	$\pm V_{CC}$	V
V_{in}	Input voltage[(3)]	V_{CC-} - 0.2 to V_{CC+}+ 0.2	V
I_{in}	Input current[(4)]	10	mA
T_{stg}	Storage temperature	-65 to +150	°C
R_{thja}	Thermal resistance junction-to-ambient[(5)],[(6)] SC70-5 DFN8 2 x 2 QFN16 3 x 3 MiniSO8 TSSOP14	 205 57 45 190 100	°C/W
T_j	Maximum junction temperature	150	°C
ESD	HBM: human body model[(7)]	4	kV
	MM: machine model[(8)]	300	V
	CDM: charged device model[(9)] (all packages except SC70-5 and DFN8)	1.5	kV
	CDM: charged device model (SC70-5 and DFN8)[(9)]	1.3	kV
	Latch-up immunity	200	mA

1. All voltage values, except differential voltages are with respect to network ground terminal.
2. Differential voltages are the non inverting input terminal with respect to the inverting input terminal.
3. V_{CC} - V_{in} must not exceed 6 V, V_{in} must not exceed 6 V.
4. Input current must be limited by a resistor in series with the inputs.
5. Short-circuits can cause excessive heating and destructive dissipation.
6. R_{th} are typical values.
7. Human body model: 100 pF discharged through a 1.5 kΩ resistor between two pins of the device, done for all couples of pin combinations with other pins floating.
8. Machine model: a 200 pF cap is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω), done for all couples of pin combinations with other pins floating.
9. Charged device model: all pins plus package are charged together to the specified voltage and then discharged directly to ground.

Table 3. Operating conditions

Symbol	Parameter	Value	Unit
V_{CC}	Supply voltage	2.7 to 5.5	V
V_{icm}	Common mode input voltage range	V_{CC-} - 0.1 to V_{CC+} + 0.1	V
T_{oper}	Operating free air temperature range	-40 to +125	°C

3 Electrical characteristics

Table 4. Electrical characteristics at V_{CC+} = +2.7 V with V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T = 25 °C, and R_L = 10 kΩ connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{io}	Offset voltage	TSV52xA, T = 25 °C			800	µV
		TSV52xA, -40 °C < T < 125 °C			2600	µV
		TSV52x, T = 25 °C			1.5	mV
		TSV52x, -40 °C < T < 125 °C			3.3	mV
$\Delta V_{io}/\Delta T$	Input offset voltage drift	-40 °C < T < 125 °C[1]		3	18	µV/°C
I_{io}	Input offset current (V_{out} = $V_{CC}/2$)	T = 25 °C		1	10[3]	pA
		-40° C < T < 125 °C		1	100[3]	pA
I_{ib}	Input bias current (V_{out} = $V_{CC}/2$)	T = 25 °C		1	10[3]	pA
		-40 °C < T < 125 °C		1	100[3]	pA
CMR	Common mode rejection ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$) V_{ic} = -0.1 V to V_{CC}+0.1V, V_{out} = $V_{CC}/2$, R_L = 1 MΩ	T = 25 °C	50	72		dB
		-40 °C < T < 125 °C	46			
A_{vd}	Large signal voltage gain V_{out} = 0.5 V to (V_{CC} - 0.5V), R_L = 1 MΩ	T = 25 °C	90	105		dB
		-40 °C < T < 125 °C	60			
V_{OH}	High level output voltage	T = 25 °C -40 °C < T < 125 °C		3	35 50	mV
V_{OL}	Low level output voltage	T = 25 °C -40 °C < T < 125 °C		6	35 50	mV
I_{out}	I_{sink}	V_{out} = V_{CC}, T = 25 °C	12	22		mA
		V_{out} = V_{CC}, -40 °C < T < 125 °C	8			
	I_{source}	V_{out} = 0 V, T = 25 °C	12	18		mA
		V_{out} = 0 V, -40 °C < T < 125 °C	8			
I_{CC}	Supply current (per channel) V_{out} = $V_{CC}/2$, R_L > 1 MΩ	T = 25 °C		30	51	µA
		-40 °C < T < 125 °C		30	51	
AC performance						
GBP	Gain bandwidth product	R_L = 10 kΩ, C_L = 100 pF	0.62	1		MHz
F_u	Unity gain frequency	R_L = 10 kΩ, C_L = 100 pF		900		kHz
Φ_m	Phase margin	R_L = 10 kΩ, C_L = 100 pF		55		degrees
G_m	Gain margin	R_L = 10 kΩ, C_L = 100 pF		7		dB
SR	Slew rate	R_L = 10 kΩ, C_L = 100 pF, V_{out} = 0.5 V to V_{CC} - 0.5 V		0.74		V/µs

Table 4. Electrical characteristics at V_{CC+} = +2.7 V with V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T = 25 °C, and R_L = 10 kΩ connected to $V_{CC}/2$ (unless otherwise specified) (continued)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
e_n	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		61 43		$\frac{nV}{\sqrt{Hz}}$
THD+N	Total harmonic distortion + noise	Follower configuration, f_{in} = 1 kHz, R_L = 100 kΩ, V_{icm} = $V_{CC}/2$, BW = 22 kHz, V_{out} = 1 V_{pp}		0.003		%

Table 5. Electrical characteristics at V_{CC+} = +3.3 V with V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T = 25 °C, and R_L = 10 kΩ connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{io}	Offset voltage	TSV52xA, T = 25 °C			600	µV
		TSV52xA, -40 °C < T < 125 °C			2400	µV
		TSV52x, T = 25 °C			1.3	mV
		TSV52x, -40 °C < T < 125 °C			3.1	mV
$\Delta V_{io}/\Delta T$	Input offset voltage drift	-40 °C < T < 125 °C(1)		3	18	µV/°C
ΔV_{io}	Long term input offset voltage drift	T = 25 °C(2)		0.3		$\frac{\mu V}{\sqrt{month}}$
I_{io}	Input offset current (V_{out} = $V_{CC}/2$)	T = 25 °C		1	10(3)	pA
		-40 °C < T < 125 °C		1	100(3)	pA
I_{ib}	Input bias current (V_{out} = $V_{CC}/2$)	T = 25 °C		1	10(3)	pA
		-40 °C < T < 125 °C		1	100(3)	pA
CMR	Common mode rejection ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$) V_{ic} = -0.1 V to V_{CC} +0.1 V, V_{out} = $V_{CC}/2$, R_L = 1 MΩ	T = 25 °C	51	73		dB
		-40 °C < T < 125 °C	47			
A_{vd}	Large signal voltage gain V_{out} = 0.5 V to (V_{CC} - 0.5 V), R_L = 1 MΩ	T = 25 °C	91	106		dB
		-40 °C < T < 125 °C	63			
V_{OH}	High level output voltage	T = 25 °C -40 °C < T < 125 °C		3	35 50	mV
V_{OL}	Low level output voltage	T = 25 °C -40 °C < T < 125 °C		7	35 50	mV
I_{out}	I_{sink}	V_{out} = V_{CC}, T = 25 °C	20	31		mA
		V_{out} = V_{CC}, -40 °C < T < 125 °C	17			
	I_{source}	V_{out} = 0 V, T = 25 °C	19	27		mA
		V_{out} = 0 V, -40 °C < T < 125 °C	17			
I_{CC}	Supply current (per channel) V_{out} = $V_{CC}/2$, R_L > 1 MΩ	T = 25 °C		32	55	µA
		-40 °C < T < 125 °C		32	55	

Table 5. Electrical characteristics at V_{CC+} = +3.3 V with V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T = 25 °C, and R_L = 10 kΩ connected to $V_{CC}/2$ (unless otherwise specified) (continued)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
AC performance						
GBP	Gain bandwidth product	R_L = 10 kΩ, C_L = 100 pF	0.64	1		MHz
F_u	Unity gain frequency	R_L = 10 kΩ, C_L = 100 pF		900		kHz
Φ_m	Phase margin	R_L = 10 kΩ, C_L = 100 pF		55		degrees
G_m	Gain margin	R_L = 10 kΩ, C_L = 100 pF		7		dB
SR	Slew rate	R_L = 10 kΩ, C_L = 100 pF, V_{out} = 0.5 V to V_{CC} - 0.5 V		0.75		V/μs
e_n	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		60 42		$\frac{nV}{\sqrt{Hz}}$
THD+N	Total harmonic distortion + noise	Follower configuration, f_{in} = 1 kHz, R_L = 100 kΩ, V_{icm} = $V_{CC}/2$, BW = 22 kHz, V_{out} = 1 V_{pp}		0.003		%

Table 6. Electrical characteristics at V_{CC+} = +5 V with V_{CC-} = 0 V, V_{icm} = $V_{CC}/2$, T = 25 °C, and R_L = 10 kΩ connected to $V_{CC}/2$ (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
DC performance						
V_{io}	Offset voltage	TSV52xA, T = 25 °C			600	μV
		TSV52xA, -40 °C < T < 125 °C			2400	μV
		TSV52x, T = 25 °C			1	mV
		TSV52x, -40 °C < T < 125 °C			2.8	mV
$\Delta V_{io}/\Delta T$	Input offset voltage drift	-40 °C < T < 125 °C(1)		3	18	μV/°C
ΔV_{io}	Long term input offset voltage drift	T = 25 °C(2)		0.7		$\frac{\mu V}{\sqrt{month}}$
I_{io}	Input offset current (V_{out} = $V_{CC}/2$)	T = 25 °C		1	10(3)	pA
		-40 °C < T < 125 °C		1	100(3)	pA
I_{ib}	Input bias current (V_{out} = $V_{CC}/2$)	T = 25 °C		1	10(3)	pA
		-40 °C < T < 125 °C		1	100(3)	pA
CMR1	Common mode rejection ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$) V_{ic} = -0.1 V to V_{CC} +0.1 V, V_{out} = $V_{CC}/2$, R_L = 1 MΩ	T = 25 °C	54	76		dB
		-40 °C < T < 125 °C	50			
CMR2	Common mode rejection ratio 20 log ($\Delta V_{ic}/\Delta V_{io}$) V_{ic} = 1 V to V_{CC} -1 V, V_{out} = $V_{CC}/2$, R_L = 1 MΩ	T = 25 °C	63	84		dB
		-40 °C < T < 125 °C	58			

Table 6. Electrical characteristics at V_{CC+} = +5 V with V_{CC-} = 0 V, V_{icm} = V_{CC}/2, T = 25 °C, and R_L = 10 kΩ connected to V_{CC}/2 (unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
SVR	Supply voltage rejection ratio 20 log ($\Delta V_{CC}/\Delta V_{io}$) V_{CC} = 2.7 V to 5.5 V, V_{out} = V_{CC}/2	T = 25 °C	65	87		dB
		-40 °C < T < 125 °C	60			
A_{vd}	Large signal voltage gain V_{out} = 0.5 V to (V_{CC} - 0.5 V), R_L = 1 MΩ	T = 25 °C	94	109		dB
		-40 °C < T < 125 °C	68			
V_{OH}	High level output voltage	T = 25 °C -40 °C < T < 125 °C		5	35 50	mV
V_{OL}	Low level output voltage	T = 25 °C -40 °C < T < 125 °C		9	35 50	mV
I_{out}	I_{sink}	V_{out} = V_{CC}, T = 25 °C	36	55		mA
		V_{out} = V_{CC}, -40 °C < T < 125 °C	27			
	I_{source}	V_{out} = 0 V, T = 25 °C	36	55		mA
		V_{out} = 0 V, -40 °C < T < 125 °C	27			
I_{CC}	Supply current (per channel) V_{out} = V_{CC}/2, R_L > 1 MΩ	T = 25 °C		45	60	µA
		-40 °C < T < 125 °C		45	60	
AC performance						
GBP	Gain bandwidth product	R_L = 10 kΩ, C_L = 100 pF	0.73	1.15		MHz
F_u	Unity gain frequency	R_L = 10 kΩ, C_L = 100 pF		900		kHz
Φ_m	Phase margin	R_L = 10 kΩ, C_L = 100 pF		55		degrees
G_m	Gain margin	R_L = 10 kΩ, C_L = 100 pF		7		dB
SR	Slew rate	R_L = 10 kΩ, C_L = 100 pF, V_{out} = 0.5 V to V_{CC} - 0.5V		0.89		V/µs
$\int e_n$	Low-frequency peak-to-peak input noise	Bandwidth: f = 0.1 to 10 Hz		14		μV_{pp}
e_n	Equivalent input noise voltage	f = 1 kHz f = 10 kHz		57 39		$\frac{nV}{\sqrt{Hz}}$
THD+N	Total harmonic distortion + noise	Follower configuration, f_{in} = 1 kHz, R_L = 100 kΩ, V_{icm} = V_{CC}/2, BW = 22 kHz, V_{out} = 1 V_{pp}		0.002		%

1. See *Section 4.6: Input offset voltage drift over temperature on page 15*.
2. Typical value is based on the V_{io} drift observed after 1000 h at 125 °C extrapolated to 25 °C using the Arrhenius law and assuming an activation energy of 0.7 eV. The operational amplifier is aged in follower mode configuration.
3. Guaranteed by design.

Figure 2. Supply current vs. supply voltage at $V_{icm} = V_{CC}/2$

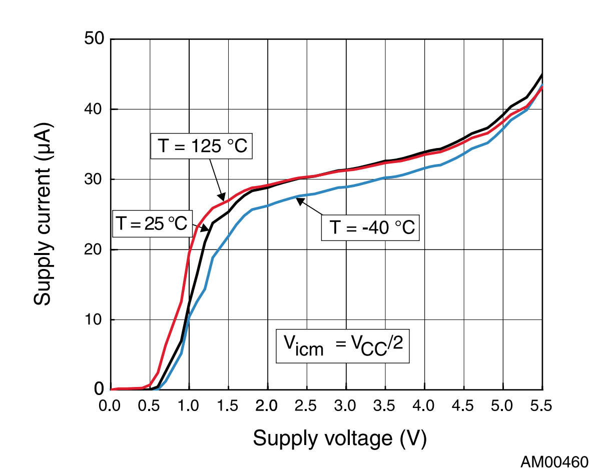


Figure 3. Input offset voltage distribution at $V_{CC} = 5$ V, $V_{icm} = 2.5$ V

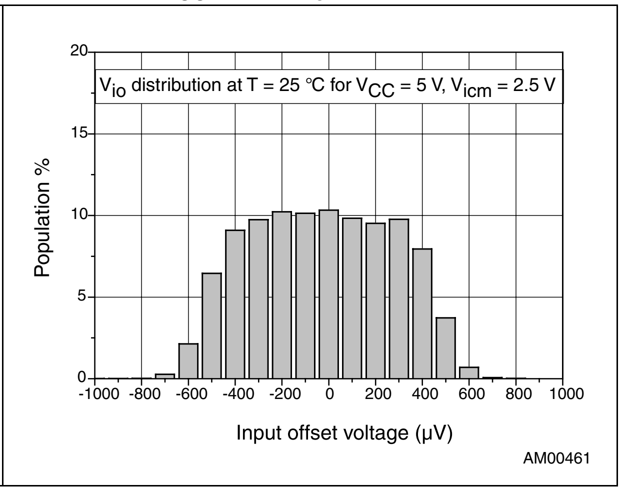


Figure 4. Input offset voltage temperature coefficient distribution

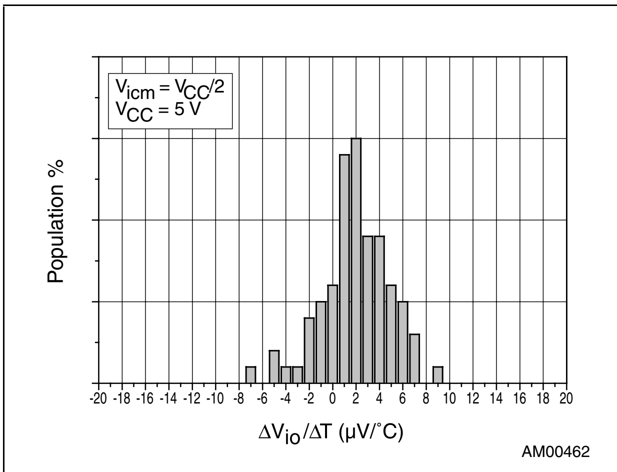


Figure 5. Input offset voltage vs. input common mode voltage at $V_{CC} = 5$ V

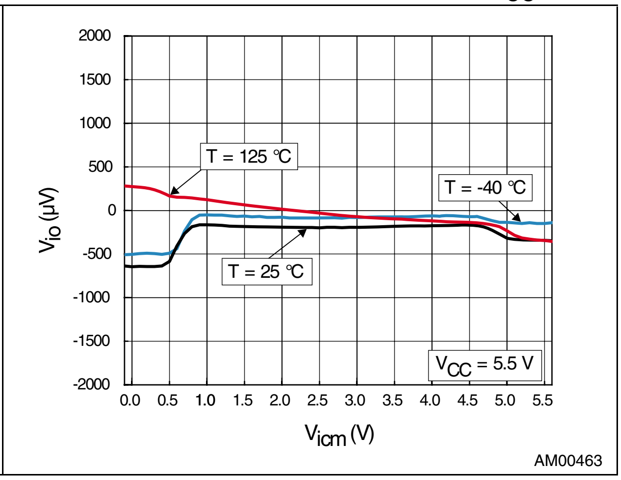


Figure 6. Input offset voltage vs. temperature at $V_{CC} = 5$ V

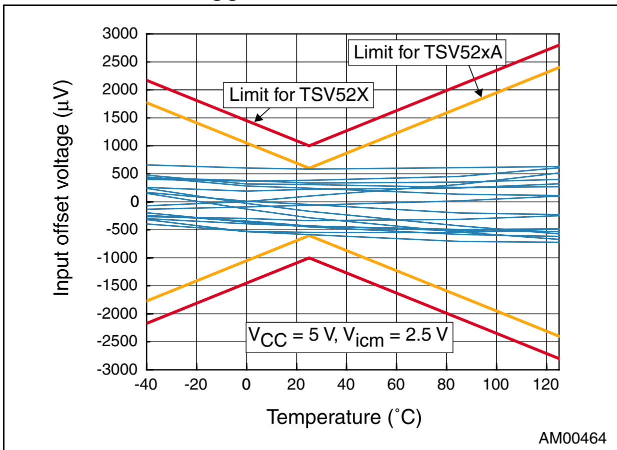


Figure 7. Output current vs. output voltage at $V_{CC} = 2.7$ V

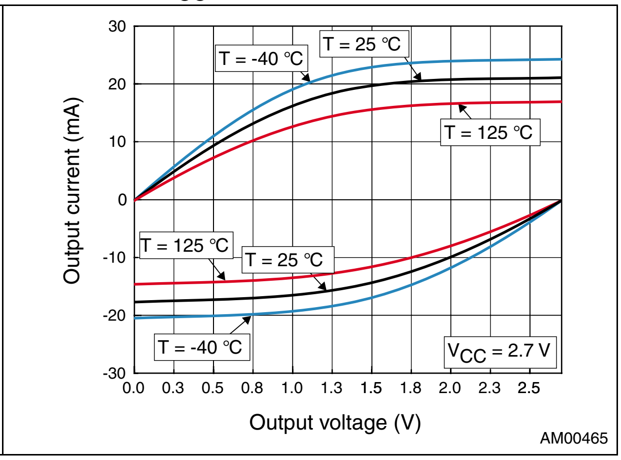


Figure 8. Output current vs. output voltage at V_{CC} = 5.5 V

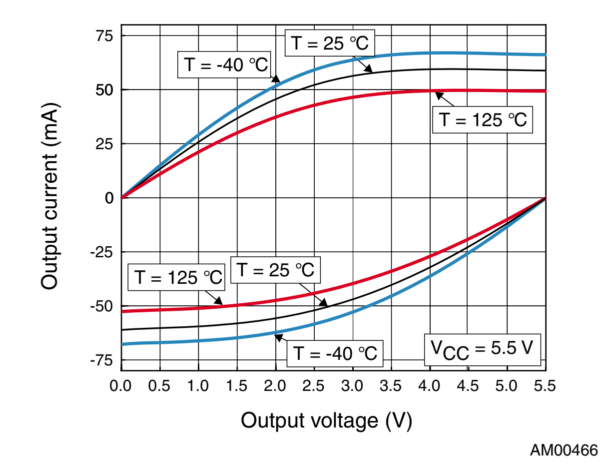


Figure 9. Bode diagram at V_{CC} = 2.7 V, R_L = 10 kΩ

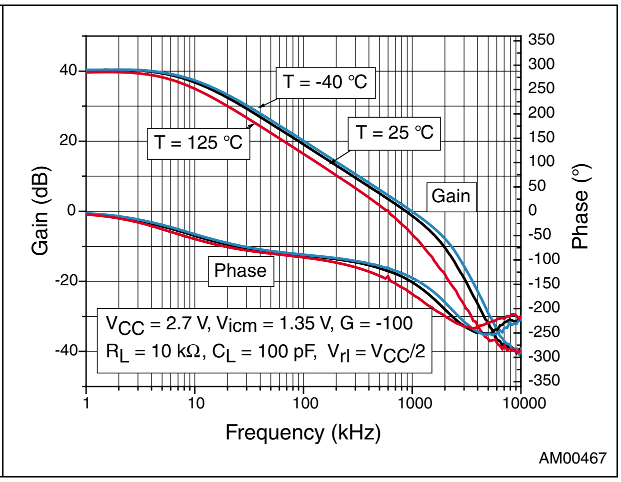


Figure 10. Bode diagram at V_{CC} = 2.7 V, R_L = 2 kΩ

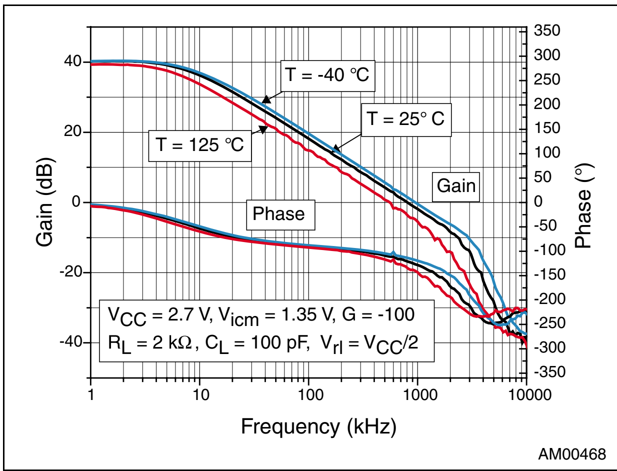


Figure 11. Bode diagram at V_{CC} = 5.5 V, R_L = 10 kΩ

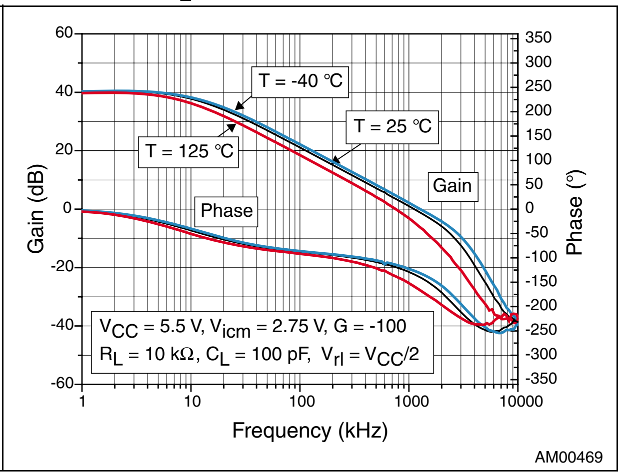


Figure 12. Bode diagram at V_{CC} = 5.5 V, R_L = 2 kΩ

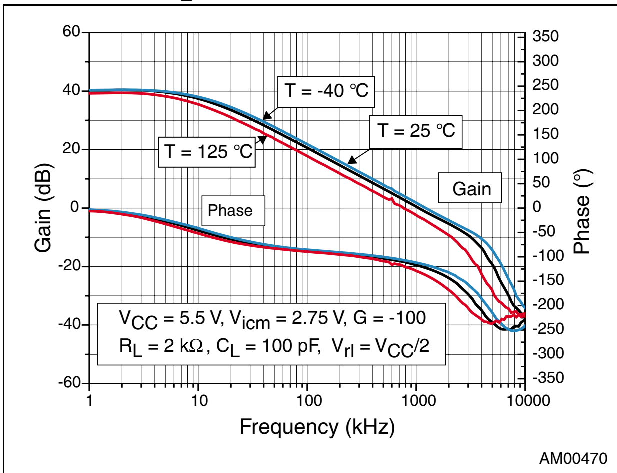


Figure 13. Noise vs. frequency

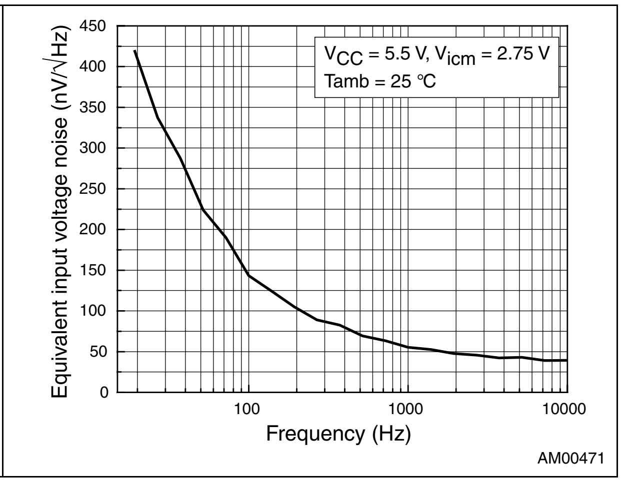


Figure 14. Positive slew rate vs. supply voltage

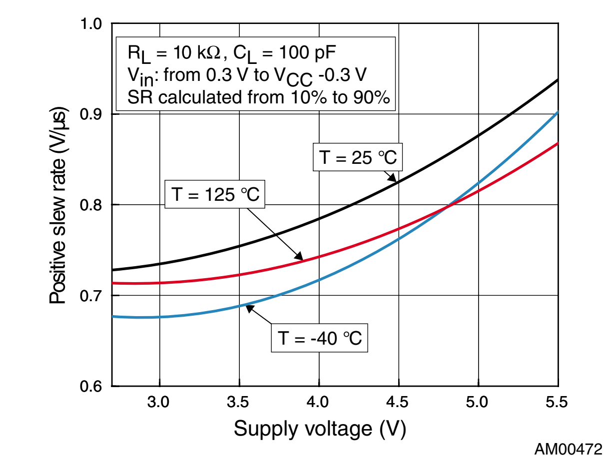


Figure 15. Negative slew rate vs. supply voltage

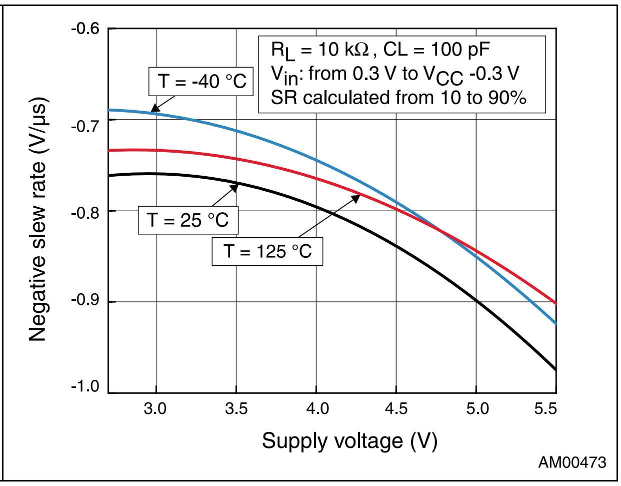


Figure 16. THD+N vs. frequency at V_{CC} = 2.7 V

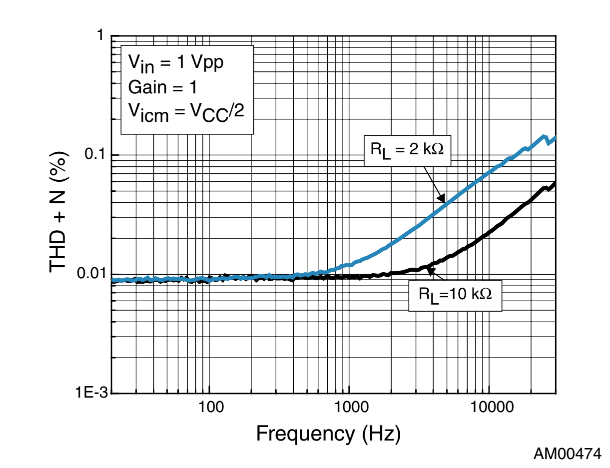


Figure 17. THD+N vs. frequency at V_{CC} = 5.5 V

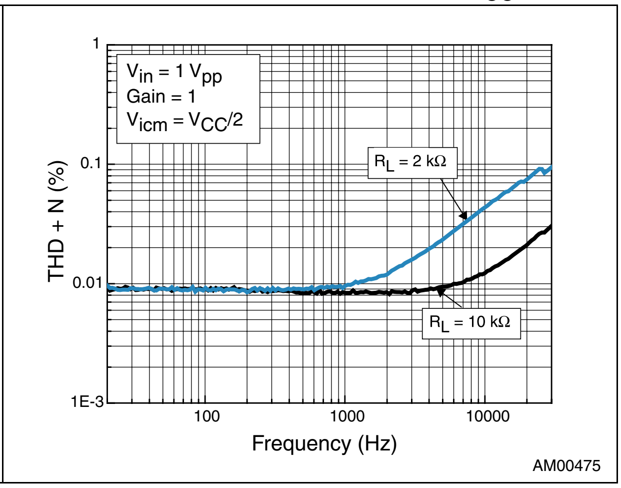


Figure 18. THD+N vs. output voltage at V_{CC} = 2.7 V

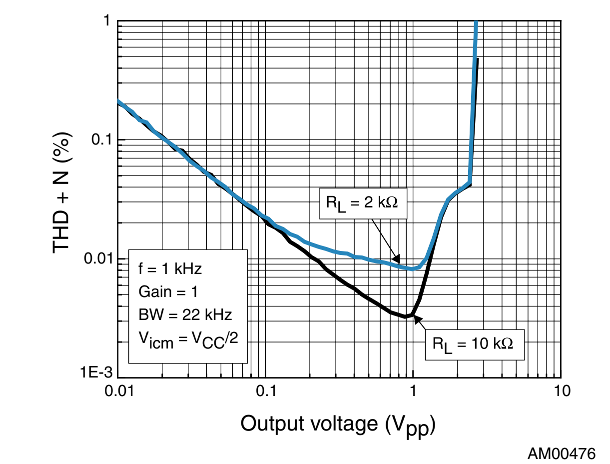


Figure 19. THD+N vs. output voltage at V_{CC} = 5.5 V

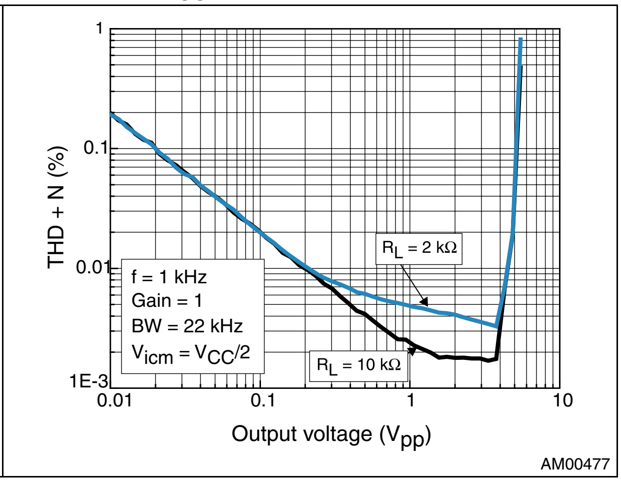


Figure 20. Output impedance versus frequency in closed-loop configuration

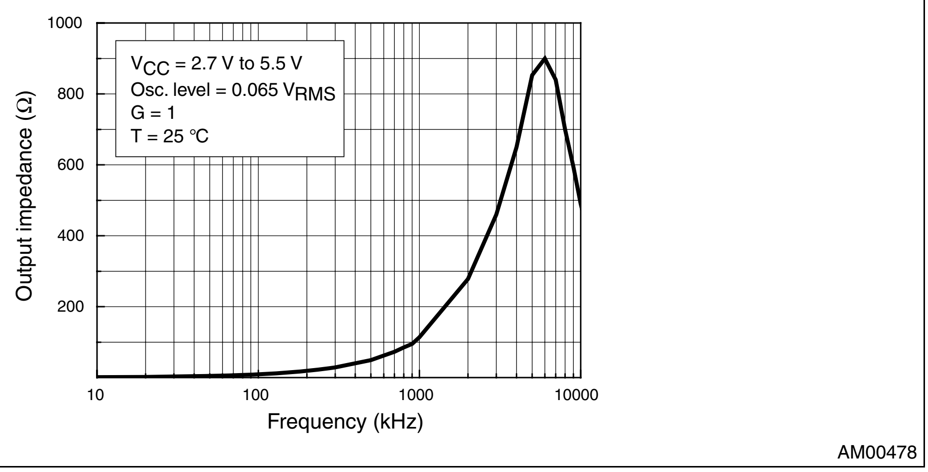


Figure 21. Response to a 100 mV input step for gain = 1 at V_{CC} = 5.5 V rising edge

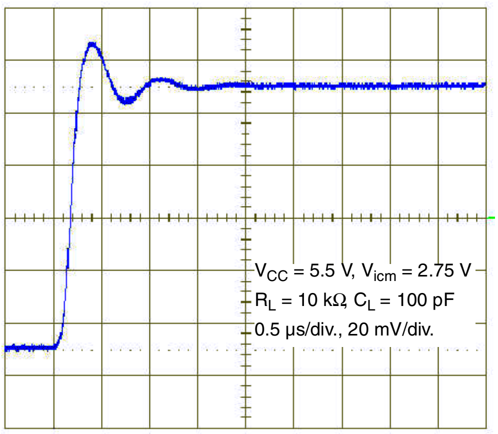


Figure 22. Response to a 100 mV input step for gain = 1 at V_{CC} = 5.5 V falling edge

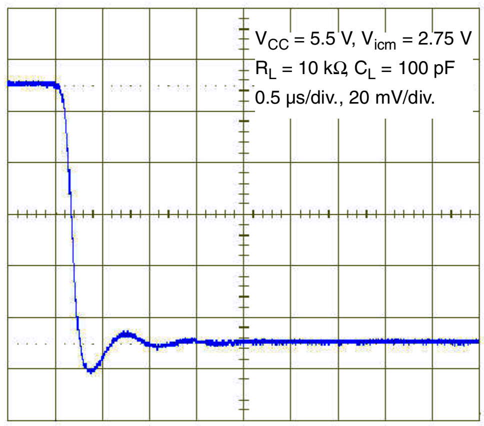


Figure 23. PSRR vs. frequency at V_{CC} = 2.7 V

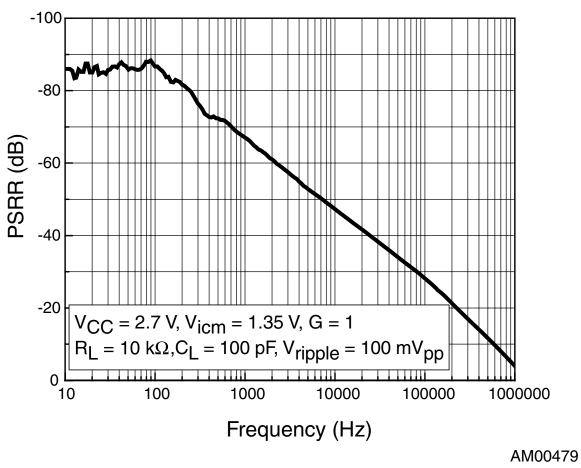
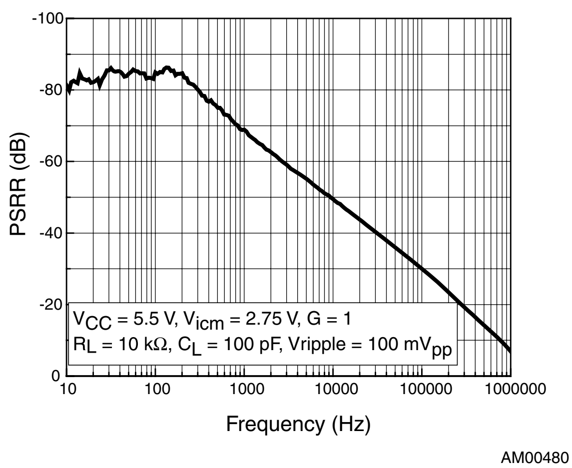


Figure 24. PSRR vs. frequency at V_{CC} = 5.5 V



4 Application information

4.1 Operating voltages

The amplifiers of the TSV52x series can operate from 2.7 to 5.5 V. Their parameters are fully specified for 2.7, 3.3 and 5 V power supplies. However, the parameters are very stable in the full V_{CC} range and several characterization curves show the TSV52x device characteristics at 2.7 V. Additionally, the main specifications are guaranteed in extended temperature ranges from -40 to +125 °C.

4.2 Common mode voltage range

The TSV52x devices are built with two complementary PMOS and NMOS input differential pairs. The devices have a rail-to-rail input and the input common mode range is extended from V_{CC-} - 0.1 V to V_{CC+} + 0.1 V.

The N channel pair is active for input voltage close to the positive rail typically (V_{CC+} - 0.7 V) to 100 mv above the positive rail.

The P channel pair is active for input voltage close to the negative rail typically 100 mV below the negative rail to V_{CC-} + 0.7 V.

And between V_{CC-} + 0.7 V and V_{CC+} - 0.7 V the both N and P pairs are active.

When the both pairs work together it allows to increase the speed of the TSV52x device. This architecture improves a lot the merit factor of the whole device. In the transition region, the performance of CMR, SVR, V_{io} (*Figure 25* and *Figure 26*) and THD is slightly degraded.

Figure 25. Input offset voltage vs. input common mode at V_{CC} = 2.7 V

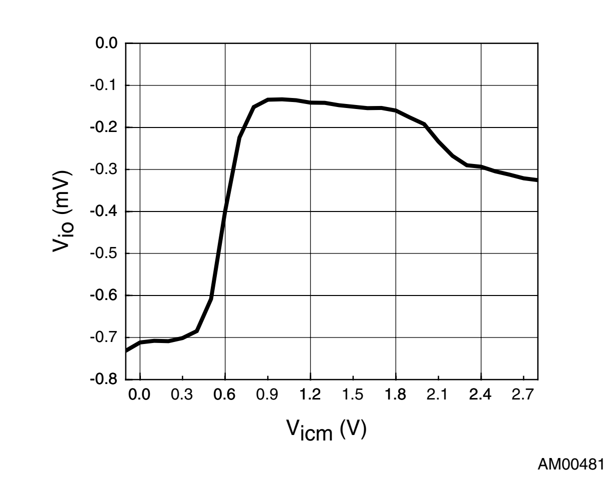
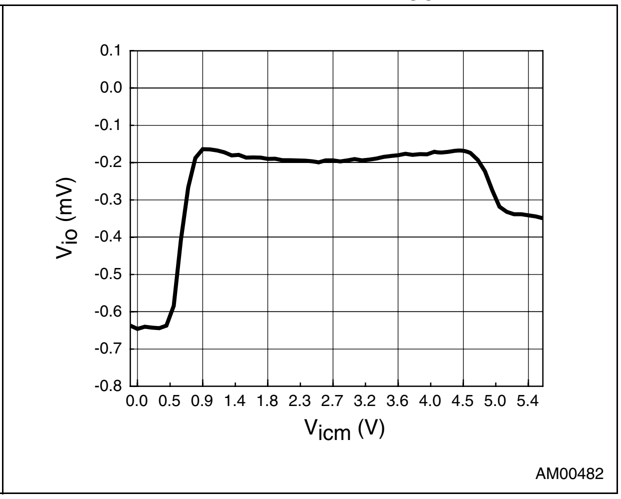


Figure 26. Input offset voltage vs. input common mode at V_{CC} = 5.5 V



4.3 Rail-to-rail input

The TSV52x series are guaranteed without phase reversal as shown in *Figure 28*.

It is extremely important that the current flowing in the input pin does not exceed 10 mA. In order to limit this current a serial resistor can be added on the V_{in} path.

Figure 27. Phase reversal test schematic

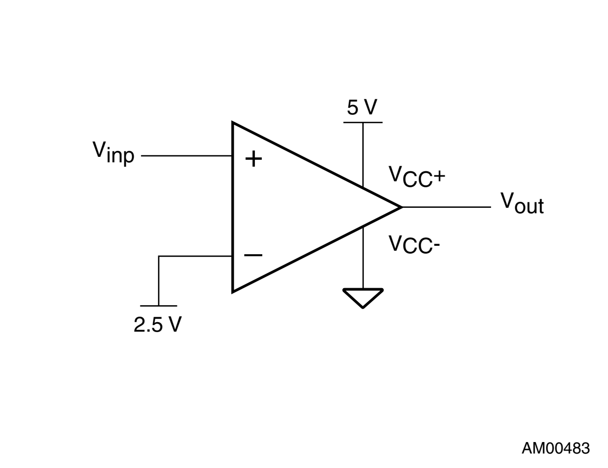
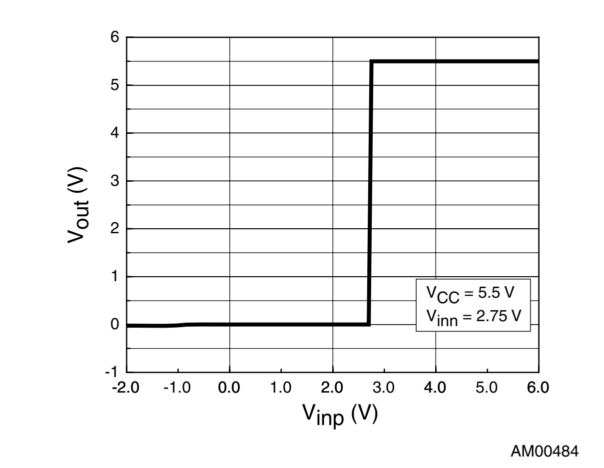


Figure 28. No phase reversal



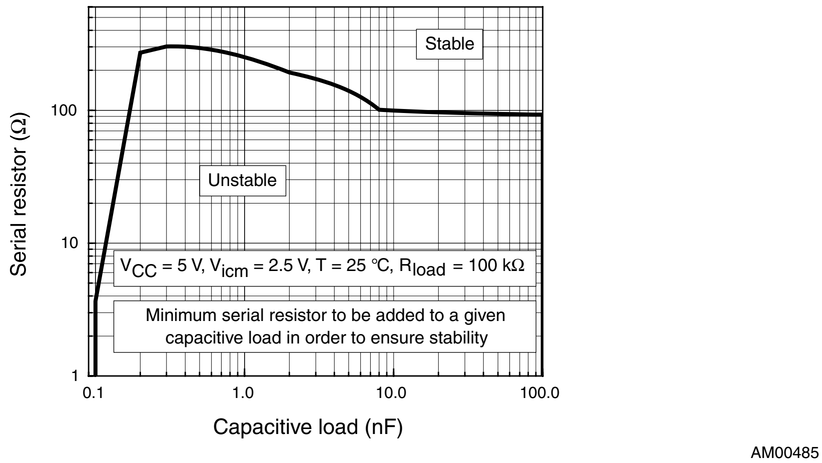
4.4 Rail-to-rail output

The operational amplifiers output levels can go close to the rails: 35 mV maximum above and below the rail when connected to a 10 kΩ resistive load to $V_{CC}/2$.

4.5 Driving resistive and capacitive loads

To drive high capacitive load, adding in series resistor at the output can improve the stability of the device (see *Figure 29* for recommended in series value). Once the in series resistor has been selected, the stability of the circuit should be tested on bench and simulated with simulation models. The R_{load} is placed in parallel with capacitive load. The R_{load} and the in series resistor create a voltage divider introducing an error proportional to the ratio R_s/R_{load}. By choosing R_s as low as possible, this error is generally negligible.

Figure 29. In series resistor versus capacitive load



4.6 Input offset voltage drift over temperature

The maximum input voltage drift over temperature variation is defined as the offset variation related to offset value measured at 25 °C. The operational amplifier is one of the main circuits of the signal conditioning chain, and the amplifier input offset is a major contributor to the chain accuracy. The signal chain accuracy at 25 °C can be compensated during production at application level. The maximum input voltage drift over temperature enables the system designer to anticipate the effects of temperature variations.

The maximum input voltage drift over temperature is computed in *Equation 1*:

Equation 1

$$\frac{\Delta V_{io}}{\Delta T} = \max\left|\frac{V_{io}(T) - V_{io}(25°C)}{T - 25°C}\right|$$

with T = -40 °C and 125 °C.

The datasheet maximum value is guaranteed by measurement on a representative sample size ensuring a Cpk greater than 2.

4.7 Long term input offset voltage drift

In a product reliability evaluation, two types of stress acceleration are usable:

- Voltage acceleration, by changing the applied voltage
- Temperature acceleration, by changing the die temperature (below the maximum junction temperature allowed by the technology) with the ambient temperature

The voltage acceleration has been defined based on JEDEC results, and is defined by:

Equation 2

$$A_{FV} = e^{\beta \cdot (V_S - V_U)}$$

where:

A_{FV} is the voltage acceleration factor

β is the voltage acceleration constant in 1/V, constant technology parameter

V_S is the stress voltage used for the accelerated test

V_U is the use voltage for the application

The temperature acceleration is driven by the Arrhenius model, and is defined by:

Equation 3

$$A_{FT} = e^{\frac{E_a}{k} \cdot \left(\frac{1}{T_U} - \frac{1}{T_S}\right)}$$

where:

A_{FT} is the temperature acceleration factor

E_a is the activation energy of the technology based on failure rate

k is the Boltzmann's constant

T_U is the temperature of the die when V_U is used

T_S is the temperature of the die under temperature stress

The final acceleration factor, A_F is the multiplication of these two acceleration factors, which is:

Equation 4

$$A_F = A_{FT} \times A_{FV}$$

Based on this A_F calculated following the defined usage temperature and usage voltage of the product, the 1000 h duration of the stress corresponds to a number of equivalent months of usage.

Equation 5

$$\text{Months} = A_F \times 1000\text{ h} \times 12\text{ months} / (24\text{h} \times 365.25\text{ days})$$

For the operational amplifier, a follower stress condition is used for the reliability evaluation, with V_{CC} defined in function of the Maximum operating voltage and the absolute maximum rating (as recommended by the JEDEC standards).

The V_{io} drift, in µV, of the product after 1000 h duration of stress is tracked with parameters at different measurement conditions, as for example:

Equation 6

$$V_{CC} = \text{max. } V_{op} \text{ with } V_{icm}=V_{CC}/2$$

Finally, knowing the calculated number of months and with the measured drift value of the V_{io} (corresponding to the electrical characteristics of the respective table) after 1000 h duration of stress, the ratio of the V_{io} drift over the square of months, ΔV_{io} in µV/√month, is defined as the long term drift parameter, the parameter estimating the reliability performance of the product.

Equation 7

$$\Delta V_{io} = V_{io} \text{ drift} / \sqrt{\text{months}}$$

4.8 PCB layouts

For correct operation, it is advised to add 10 nF decoupling capacitors as close as possible to the power supply pins.

4.9 Macromodel

Accurate macromodels of the TSV52x device are available on STMicroelectronics™ website at www.st.com. This model is a trade-off between accuracy and complexity (that is, time simulation) of the TSV52x operational amplifiers. It emulates the nominal performance of a typical device within the specified operating conditions mentioned in the datasheet. It also helps to validate a design approach and to select the appropriate operational amplifier, *but it does not replace onboard measurements*.

5 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK is an ST trademark.

Figure 30. SC70-5 package outline

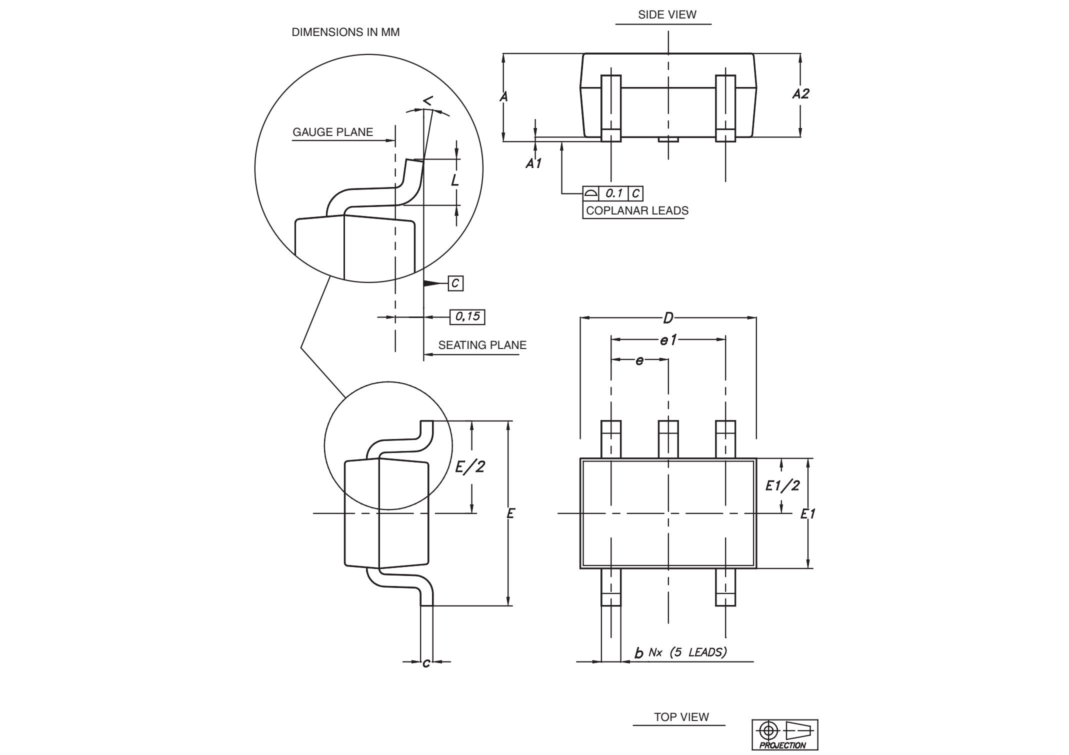


Table 7. SC70-5 package mechanical data

Ref	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.80		1.10	0.032		0.043
A1	0		0.10			0.004
A2	0.80	0.90	1.00	0.032	0.035	0.039
b	0.15		0.30	0.006		0.012
c	0.10		0.22	0.004		0.009
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E1	1.15	1.25	1.35	0.045	0.049	0.053
e		0.65			0.025	
e1		1.30			0.051	
L	0.26	0.36	0.46	0.010	0.014	0.018
<	0°		8°			

Figure 31. DFN8 2 x 2 x 0.6, 8 pitch, 0.5 mm package outline

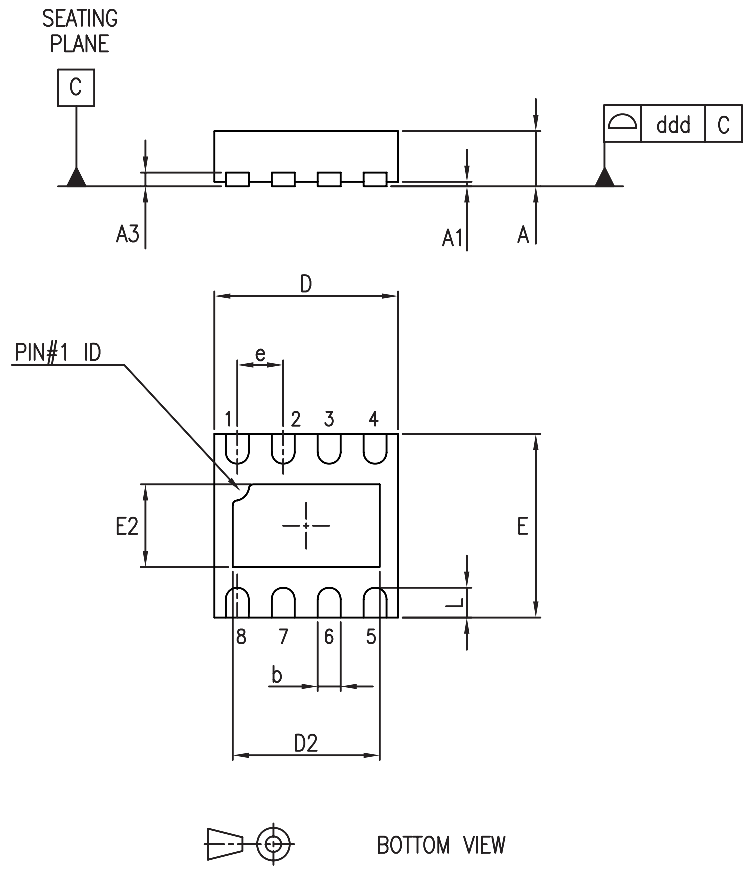


Table 8. DFN8 2 x 2 x 0.6, 8 pitch, 0.5 mm package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.51	0.55	0.60	0.020	0.022	0.024
A1			0.05			0.002
A3		0.15			0.006	
b	0.18	0.25	0.30	0.007	0.010	0.012
D	1.85	2.00	2.15	0.073	0.079	0.085
D2	1.45	1.60	1.70	0.057	0.063	0.067
E	1.85	2.00	2.15	0.073	0.079	0.085
E2	0.75	0.90	1.00	0.030	0.035	0.039
e		0.50			0.020	
L			0.50			0.020
ddd			0.08			0.003

Figure 32. DFN8 2 x 2 0.6, 8 pitch, 0.5 mm footprint recommendation

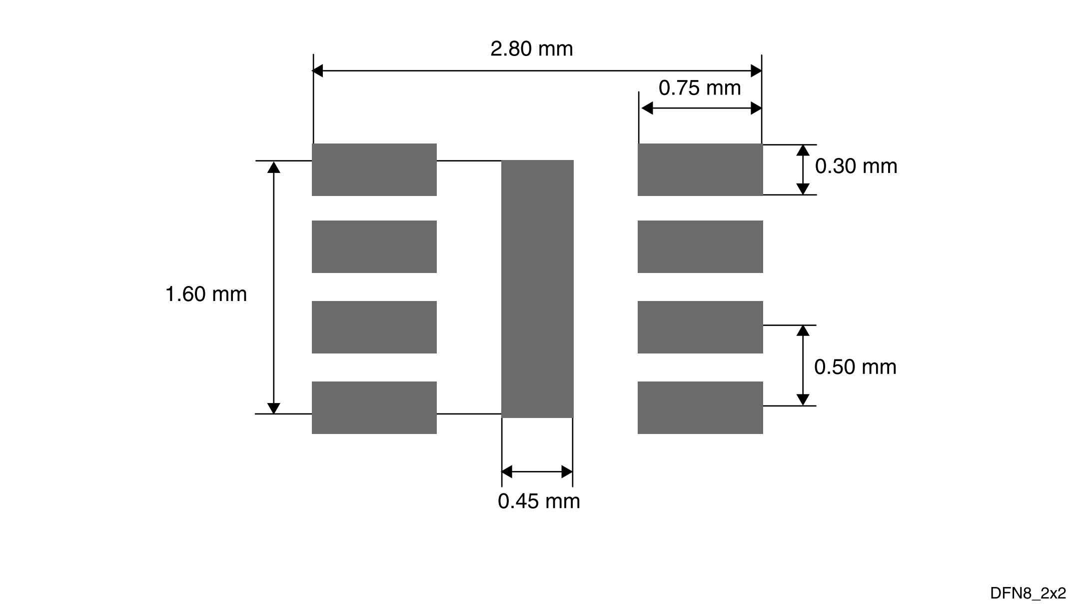


Figure 33. MiniSO8 package outline

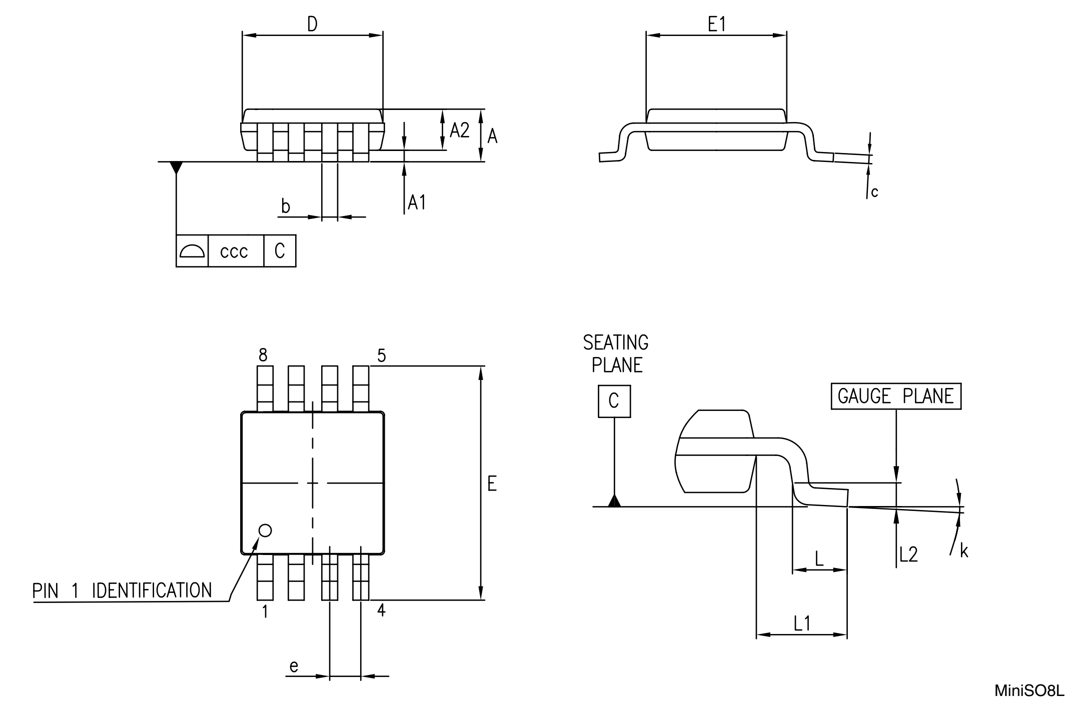


Table 9. MiniSO8 package mechanical data

Symbol	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.10			0.043
A1	0		0.15	0		0.006
A2	0.75	0.85	0.95	0.030	0.033	0.037
b	0.22		0.40	0.009		0.016
c	0.08		0.23	0.003		0.009
D	2.80	3.00	3.20	0.11	0.118	0.126
E	4.65	4.90	5.15	0.183	0.193	0.203
E1	2.80	3.00	3.10	0.11	0.118	0.122
e		0.65			0.026	
L	0.40	0.60	0.80	0.016	0.024	0.031
L1		0.95			0.037	
L2		0.25			0.010	
k	0°		8°	0°		8°
ccc			0.10			0.004

Figure 34. QFN16 - 3 x 3 x 0.9 mm, pad 1.7 - package outline

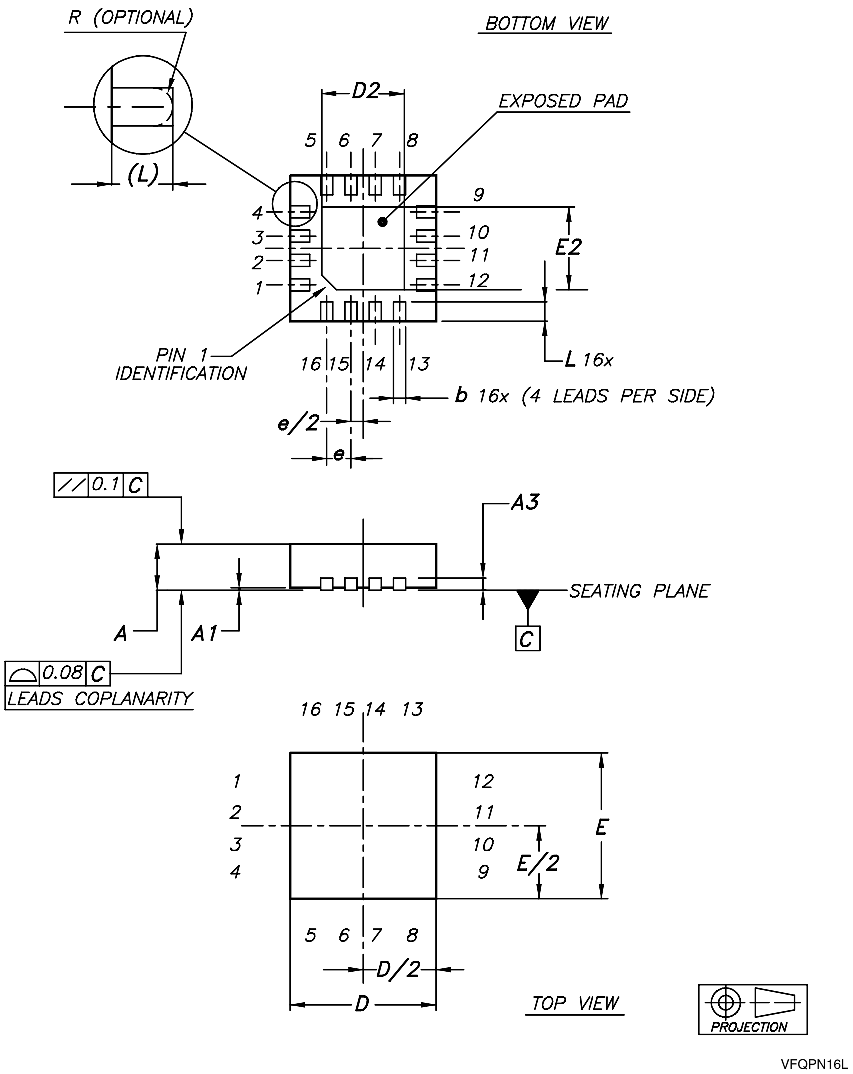


Table 10. QFN16 - 3 x 3 x 0.9 mm, pad 1.7 - package mechanical data

Symbol	Dimensions					
	Millimeters			Inches		
	Nom.	Min.	Max.	Nom.	Min.	Max.
A	0.90	0.80	1.00	0.035	0.032	0.039
A1		0.00	0.05		0.000	0.002
A3	0.20			0.008		
b		0.18	0.30		0.007	0.012
D	3.00	2.90	3.10	0.118	0.114	0.122
D2		1.50	1.80		0.061	0.071
E	3.00	2.90	3.10	0.118	0.114	0.122
E2		1.50	1.80		0.061	0.071
e	0.50			0.020		
L		0.30	0.50		0.012	0.020

Figure 35. QFN16 - 3 x 3 x 0.9 mm, pad 1.7 - footprint recommendation

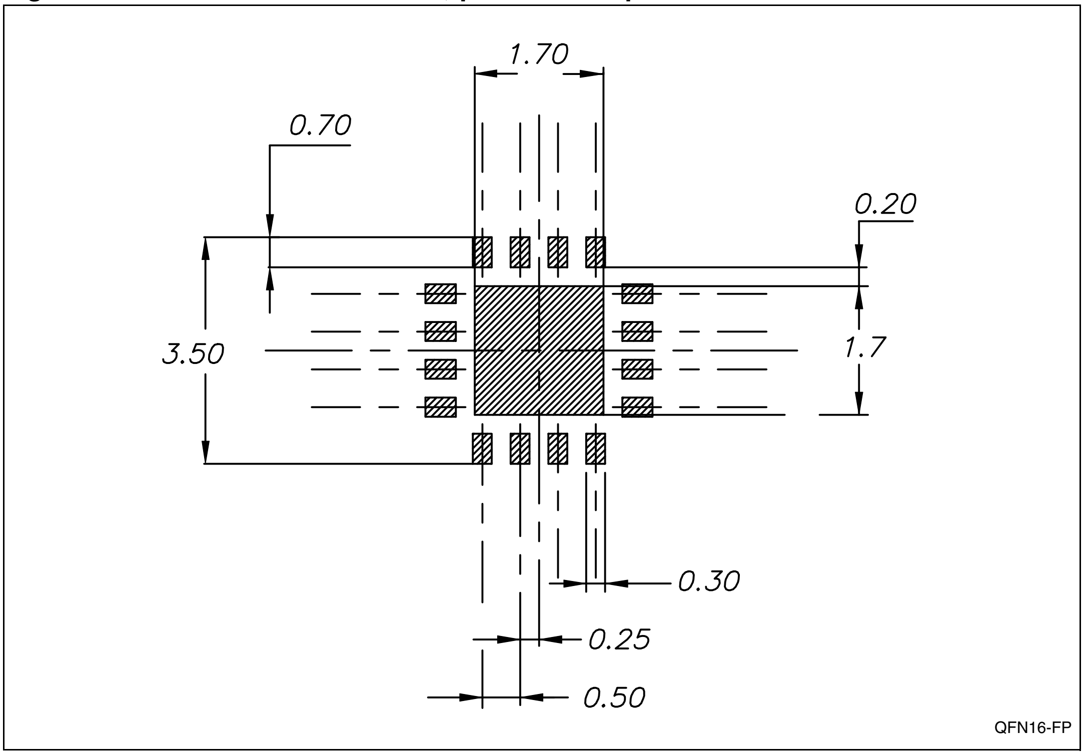


Figure 36. TSSOP14 body 4.40 mm, lead pitch 0.65 mm - package outline

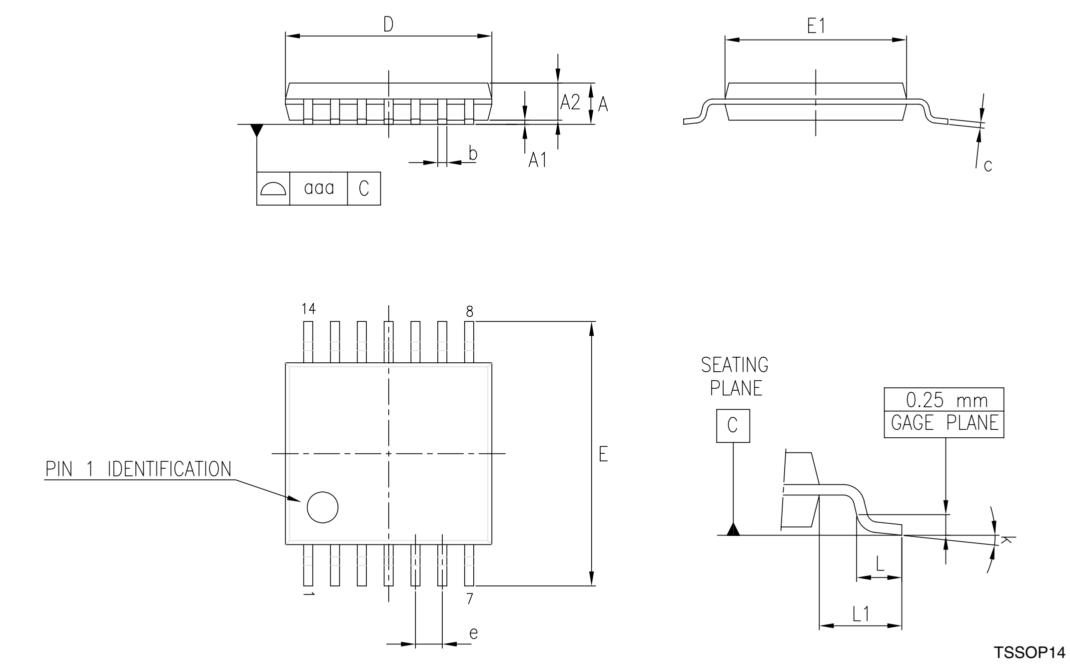


Table 11. TSSOP14 body 4.40 mm, lead pitch 0.65 mm - package mechanical data

Symbol	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.20			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.90	5.00	5.10	0.193	0.197	0.201
E	6.20	6.40	6.60	0.244	0.252	0.260
E1	4.30	4.40	4.50	0.169	0.173	0.176
e		0.65			0.0256 BSC	
L	0.45	0.60	0.75			
L1		1.00				
k	0°		8°	0°		8°
aaa			0.10	0.018	0.024	0.030

6 Ordering information

Table 12. Order codes

Order code	Temperature range	Package	Packing	Marking
TSV521ICT	-40 to 125 °C	SC70-5	Tape and reel	K1G
TSV522IQ2T		DFN8 2 x 2		K1G
TSV522IST		MiniSO8		K1G
TSV524IQ4T		QFN16 3 x 3		K1G
TSV524IPT		TSSOP14		TSV524
TSV522IYST	-40 to 125 °C Automotive grade(1)	MiniSO8	Tape and reel	K1H
TSV524IYPT		TSSOP14		TSV524Y
TSV521AICT	-40 to 125 °C	SC70-5	Tape and reel	K1K
TSV522AIQ2T		DFN8 2 x 2		K1K
TSV522AIST		MiniSO8		K1K
TSV524AIQ4T		QFN16 3 x 3		K1K
TSV524AIPT		TSSOP14		TSV524A
TSV522AIYST	-40 to 125 °C Automotive grade(1)	MiniSO8	Tape and reel	K1L
TSV524AIYPT		TSSOP14		TSV524AY

1. Qualification and characterization according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q 002 or equivalent are ongoing.

7 Revision history

Table 13. Document revision history

Date	Revision	Changes
19-Jun-2012	1	Initial release.

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